## Low Power, Standard Frequency Oscillator



### **Features**

- 51 standard frequencies between 3.75 MHz and 77.76 MHz
- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 PPM
- Low power consumption of 3.6 mA typical
- Standby mode for longer battery life
- Fast startup time of 5 ms
- LVCMOS/HCMOS compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- Pb-free, RoHS and REACH compliant

## **Applications**

- Ideal for DSC, DVC, DVR, IP CAM, Tablets, e-Books, SSD, GPON, EPON, etc
- Ideal for high-speed serial protocols such as: USB, SATA, SAS, Firewire, 100M / 1G / 10G Ethernet, etc.







## Electrical Characteristics<sup>[1]</sup>

Parameter and Conditions	Symbol	Min.	Тур.	Max.	Unit	Condition
			F	requency Ra	ange	
Output Frequency Range	f	(Refer to th	e frequency	list page 10)	MHz	51 standard frequencies between 3.75 MHz and 77.76 MHz
	•	•	Freque	ncy Stability	and Aging	3
Frequency Stability	F_stab	-20	-	+20	PPM	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and
		-25	-	+25	PPM	variations over operating temperature, rated power supply voltage and load.
		-50	_	+50	PPM	Voltage and load.
	•	•	Operati	ng Tempera	ture Range	)
Operating Temperature Range	T_use	-20	_	+70	°C	Extended Commercial
		-40	_	+85	°C	Industrial
	•	Sı	upply Voltag	ge and Curre	nt Consur	nption
Supply Voltage	Vdd	1.62	1.8	1.98	V	Contact SiTime for 1.5V support
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.7	3.0	3.3	V	
		2.97	3.3	3.63	V	
		2.25	_	3.63	V	
Current Consumption	ldd	_	3.8	4.5	mA	No load condition, f = 20 MHz, Vdd = 2.8V to 3.3V
		_	3.6	4.2	mA	No load condition, f = 20 MHz, Vdd = 2.5V
		_	3.4	3.9	mA	No load condition, f = 20 MHz, Vdd = 1.8V
OE Disable Current	I_OD	-	-	4	mA	Vdd = 2.5V to 3.3V, OE = GND, output is Weakly Pulled Down
		-	-	3.8	mA	Vdd = 1.8 V. OE = GND, output is Weakly Pulled Down
Standby Current	I_std	-	2.6	4.3	μΑ	ST = GND, Vdd = 2.8V to 3.3V, Output is Weakly Pulled Down
		-	1.4	2.5	μΑ	ST = GND, Vdd = 2.5V, Output is Weakly Pulled Down
		-	0.6	1.3	μА	ST = GND, Vdd = 1.8V, Output is Weakly Pulled Down
			LVCMOS	Output Cha	racteristic	es
Duty Cycle	DC	45	-	55	%	All Vdds
Rise/Fall Time	Tr, Tf	-	1	2	ns	Vdd = 2.5V, 2.8V, 3.0V or 3.3V, 20% - 80%
		-	1.3	2.5	ns	Vdd =1.8V, 20% - 80%
		-	-	2	ns	Vdd = 2.25V - 3.63V, 20% - 80%
Output High Voltage	VOH	90%	_	_	Vdd	IOH = -4 mA (Vdd = 3.0V or 3.3V) IOH = -3 mA (Vdd = 2.8V and Vdd = 2.5V) IOH = -2 mA (Vdd = 1.8V)
Output Low Voltage	VOL	-	-	10%	Vdd	IOL = 4 mA (Vdd = 3.0V or 3.3V) IOL = 3 mA (Vdd = 2.8V and Vdd = 2.5V) IOL = 2 mA (Vdd = 1.8V)
	1		Inp	ut Characte	ristics	•
Input High Voltage	VIH	70%	_	-	Vdd	Pin 1, OE or ST
Input Low Voltage	VIL	_	-	30%	Vdd	Pin 1, OE or ST
Input Pull-up Impedence	Z_in	-	87	100	kΩ	Pin 1, OE logic high or logic low, or ST logic high
		2	-	-	MΩ	Pin 1, ST logic low

#### Note:

SiTime Corporation 990 Almanor Avenue Sunnyvale, CA 94085 Revised March 26, 2015 Rev. 1.2

www.sitime.com (408) 328-4400

<sup>1.</sup> All electrical specifications in the above table are specified with 15 pF output load and for all Vdd(s) unless otherwise stated.

## Low Power, Standard Frequency Oscillator



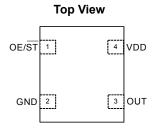
## Electrical Characteristics<sup>[1]</sup> (continued)

Parameter and Conditions	Symbol	Min.	Тур.	Max.	Unit	Condition			
Startup and Resume Timing									
Startup Time	T_start	-	-	5	ms	Measured from the time Vdd reaches its rated minimum value			
Enable/Disable Time	T_oe	-	-	130	ns	f = 110 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles			
Resume Time	T_resume	-	-	5	ms	Measured from the time ST pin crosses 50% threshold			
Startup Time	T_start	-	-	5	ms	Measured from the time Vdd reaches its rated minimum value			
	'			Jitter	•				
RMS Period Jitter	T_jitt	-	1.76	3	ps	f = 75 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V			
		-	1.78	3	ps	f = 75 MHz, Vdd = 1.8V			
RMS Phase Jitter (random)	T_phj	-	0.5	0.9	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz			
		-	1.3	2	ps	f = 75 MHz, Integration bandwidth = 12 kHz to 20 MHz			

#### Notes:

## **Pin Description**

Pin	Symbol		Functionality
1	OE/ ST	Output Enable	H or Open <sup>[2]</sup> : specified frequency output L: output is high impedance. Only output driver is disabled.
1		Standby	H or Open <sup>[2]</sup> : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I_std.
2	GND	Power	Electrical ground <sup>[3]</sup>
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage <sup>[3]</sup>



#### Notes:

2. A pull-up resistor of <10 k $\Omega$  between OE/  $\overline{\text{ST}}$  pin and Vdd is recommended in high noise environment. 3. A capacitor value of 0.1  $\mu\text{F}$  between Vdd and GND is required.

## **Absolute Maximum**

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C
Junction Temperature	-	150	°C

## **Thermal Consideration**

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	191	263	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	124	227	26

## **Environmental Compliance**

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

<sup>1.</sup> All electrical specifications in the above table are specified with 15 pF output load and for all Vdd(s) unless otherwise stated.



## Test Circuit and Waveform<sup>[4]</sup>

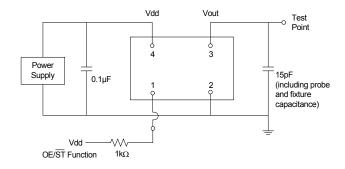


Figure 1. Test Circuit

### Note:

4. Duty Cycle is computed as Duty Cycle = TH/Period.

## 50% 20% Vdd High Pulse Low Pulse (TH) Period

Figure 2. Waveform

## **Timing Diagram**

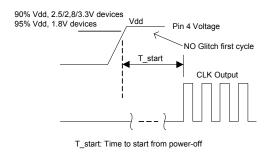


Figure 3. Startup Timing (OE/ST Mode)

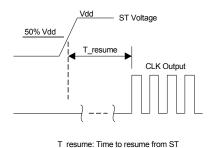


Figure 4. Standby Resume Timing (ST Mode Only)

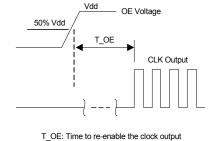
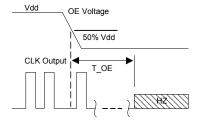


Figure 5. OE Enable Timing (OE Mode Only)



T\_OE: Time to put the output drive in High Z mode

Figure 5. OE Disable Timing (OE Mode Only)

### Notes:

- 5. SiT1602 supports "no runt" pulses and "no glitch" output during startup or resume.
- 6. SiT1602 supports gated output which is accurate within rated frequency stability from the first cycle.



## **Performance Plots**

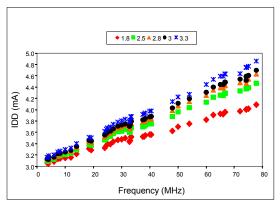


Figure 7. IDD vs Frequency

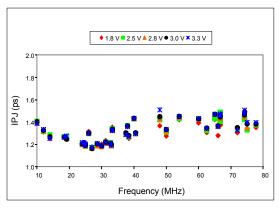


Figure 9. RMS Phase Jitter vs Frequency (12 kHz to 20 MHz Integration Bandwidth)

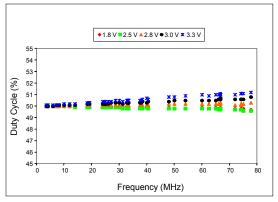


Figure 11. Duty Cycle vs Frequency

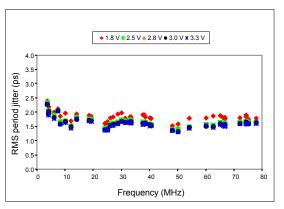


Figure 8. RMS Period Jitter vs Frequency

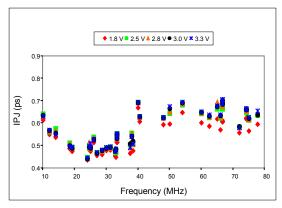


Figure 10. RMS Phase Jitter vs Frequency (900 kHz to 20 MHz Integration Bandwidth)

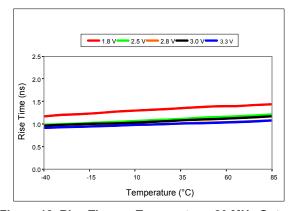


Figure 12. Rise Time vs Temperature, 20 MHz Output

### Note:

7. All plots are measured with 15 pF load at room temperature, unless otherwise stated.

## Low Power, Standard Frequency Oscillator



## **Programmable Drive Strength**

The SiT1602 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Applications Note section; http://www.sitime.com/support/application-notes.

### **EMI Reduction by Slowing Rise/Fall Time**

Figure 13 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

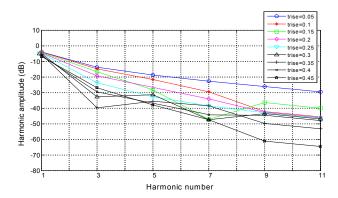


Figure 13. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

### Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to increase rise/fall time (edge rate) of the input clock. Some chipsets would require faster rise/fall time in order to reduce their sensitivity to this type of jitter. The SiT1602 provides up to 3 additional high drive strength settings for very fast rise/fall time. Refer to the Rise/Fall Time Tables to determine the proper drive strength.

### **High Output Load Capability**

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3V SiT1602 device with default drive strength setting, the typical rise/fall time is 1ns for 15 pF output load. The typical rise/fall time slows down to 2.6ns when the output load increases to 45 pF. One can

choose to speed up the rise/fall time to 1.68ns by then increasing the drive strength setting on the SiT1602.

The SiT1602 can support up to 60 pF or higher in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the Rise/Tall Time Tables to determine the proper drive strength for the desired combination of output load vs. rise/fall time

### SiT1602 Drive Strength Selection

Tables 1 through 5 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the SiT1602 nominal supply voltage (1.8V, 2.5V, 2.8V, 3.0V, 3.3V).
- Select the capacitive load column that matches the application requirement (5 pF to 60 pF)
- 3. Under the capacitive load column, select the desired rise/fall times.
- 4. The left-most column represents the part number code for the corresponding drive strength.
- Add the drive strength code to the part number for ordering purposes.

### **Calculating Maximum Frequency**

Based on the rise and fall time data given in Tables 1 through 4, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

Max Frequency = 
$$\frac{1}{5 \times Trf \ 20/80}$$

Where Trf\_20/80 is the typical rise/fall time at 20% to 80% Vdd

### Example 1

Calculate f<sub>MAX</sub> for the following condition:

- Vdd = 1.8V (Table 1)
- · Capacitive Load: 30 pF
- Desired Tr/f time = 3 ns (rise/fall time part number code = E)

Part number for the above example:

SiT1602AIE12-18E-66.666660



Drive strength code is inserted here. Default setting is "-"

## Low Power, Standard Frequency Oscillator



## Rise/Fall Time (20% to 80%) vs $C_{LOAD}$ Tables

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	6.16	11.61	22.00	31.27	39.91			
Α	3.19	6.35	11.00	16.01	21.52			
R	2.11	4.31	7.65	10.77	14.47			
В	1.65	3.23	5.79	8.18	11.08			
T	0.93	1.91	3.32	4.66	6.48			
E	0.78	1.66	2.94	4.09	5.74			
U	0.70	1.48	2.64	3.68	5.09			
F or "-": default	0.65	1.30	2.40	3.35	4.56			

Table 1	Vdd = 1.8V	Rise/Fall	Times for	Specific	C
I able I.	. vuu – 1.0v	13136/1 all	I IIIIES IOI	Specific	

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	4.13	8.25	12.82	21.45	27.79			
Α	2.11	4.27	7.64	11.20	14.49			
R	1.45	2.81	5.16	7.65	9.88			
В	1.09	2.20	3.88	5.86	7.57			
T	0.62	1.28	2.27	3.51	4.45			
E or "-": default	0.54	1.00	2.01	3.10	4.01			
U	0.43	0.96	1.81	2.79	3.65			
F	0.34	0.88	1.64	2.54	3.32			

Table 2. Vdd = 2.5V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub>	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.77	7.54	12.28	19.57	25.27			
Α	1.94	3.90	7.03	10.24	13.34			
R	1.29	2.57	4.72	7.01	9.06			
В	0.97	2.00	3.54	5.43	6.93			
T	0.55	1.12	2.08	3.22	4.08			
E or "-": default	0.44	1.00	1.83	2.82	3.67			
U	0.34	0.88	1.64	2.52	3.30			
F	0.29	0.81	1.48	2.29	2.99			

Table 3. Vdd = 2.8V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)								
Drive Strength $\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	5 pF	15 pF	30 pF	45 pF	60 pF			
L	3.60	7.21	11.97	18.74	24.30			
Α	1.84	3.71	6.72	9.86	12.68			
R	1.22	2.46	4.54	6.76	8.62			
В	0.89	1.92	3.39	5.20	6.64			
T or "-": default	0.51	1.00	1.97	3.07	3.90			
E	0.38	0.92	1.72	2.71	3.51			
U	0.30	0.83	1.55	2.40	3.13			
F	0.27	0.76	1.39	2.16	2.85			

Table 4. Vdd = 3.0V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)							
Drive Strength $\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	30 pF	45 pF	60 pF				
L	3.39	6.88	11.63	17.56	23.59		
Α	1.74	3.50	6.38	8.98	12.19		
R	1.16	2.33	4.29	6.04	8.34		
В	0.81	1.82	3.22	4.52	6.33		
T or "-": default	0.46	1.00	1.86	2.60	3.84		
E	0.33	0.87	1.64	2.30	3.35		
U	0.28	0.79	1.46	2.05	2.93		
F	0.25	0.72	1.31	1.83	2.61		

Table 5. Vdd = 3.3V Rise/Fall Times for Specific  $C_{LOAD}$ 

## Low Power, Standard Frequency Oscillator



# Instant Samples with Time Machine and Field Programmable Oscillators

SiTime supports a field programmable version of the SiT1602 low power oscillator for fast prototyping and real time customization of features. The <u>field programmable devices</u> (FP devices) are available for all five standard SiT1602 package sizes and can be configured to one's exact specification using the <u>Time Machine II</u>, an USB powered MEMS oscillator programmer.

### Customizable Features of the SiT1602 FP Devices Include

- 51 standard frequencies between 3.75 MHz and 77.76MHz (Refer to the frequency list page 10)
- Three frequency stability options, ±20 PPM, ±25 PPM, ±50 PPM
- Two operating temperatures, -20 to 70°C or -40 to 85°C
- Five supply voltage options, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V and 2.25 to 3.65V continuous

· Output drive strength

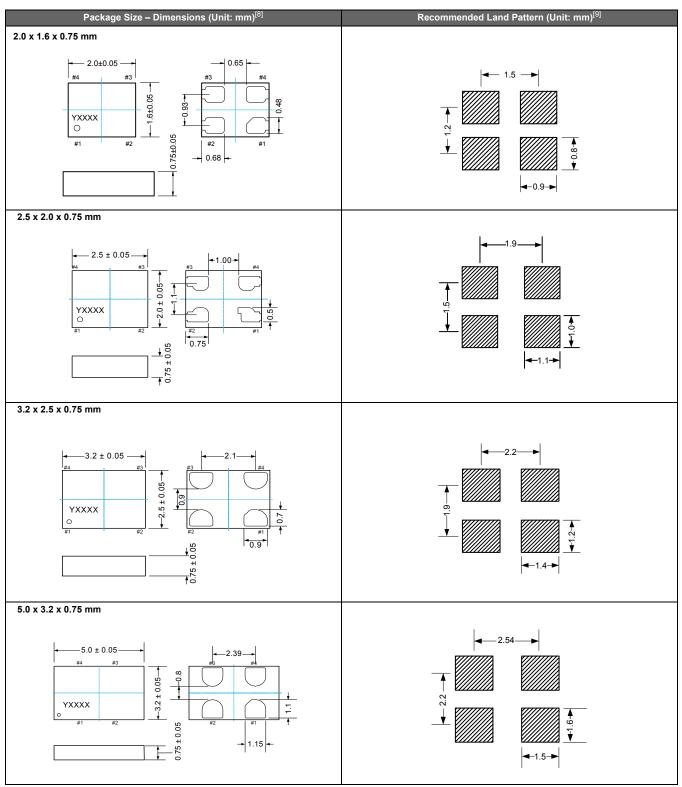
For more information regarding SiTime's field programmable solutions, visit <a href="http://www.sitime.com/time-machine">http://www.sitime.com/tp-devices</a>.

SiT1602 is typically factory-programmed per customer ordering codes for volume delivery.

## Low Power, Standard Frequency Oscillator



## **Dimensions and Patterns**

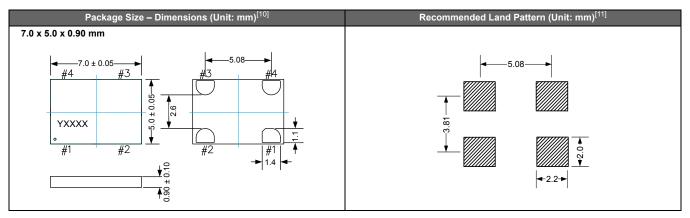


8. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device. 9. A capacitor of value 0.1 µF between Vdd and GND is required.

## Low Power, Standard Frequency Oscillator



## **Dimensions and Patterns**



### Notes:

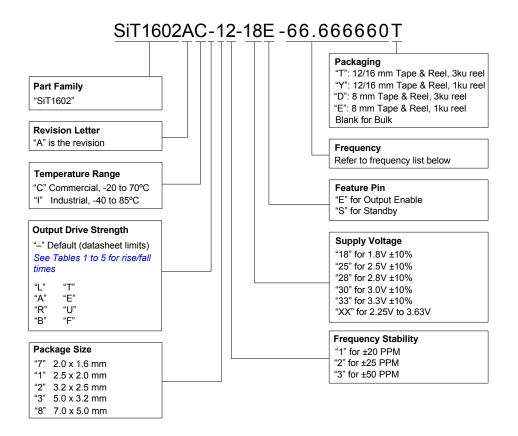
- 10. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 11. A capacitor of value 0.1 µF between Vdd and GND is required.

## Low Power, Standard Frequency Oscillator



## Ordering Information

The Part No. Guide is for reference only. To customize and build an exact part number, use the SiTime Part Number Generator.



## Supported Frequencies<sup>[12]</sup>

3.57 MHz	4 MHz	4.096 MHz	6 MHz	7.3728 MHz	8.192 MHz	10 MHz	12 MHz	14 MHz
18.432 MHz	19.2 MHz	20 MHz	24 MHz	24.576 MHz	25 MHz	25.000625 MHz	26 MHz	27 MHz
28.6363 MHz	30 MHz	31.25 MHz	32.768 MHz	33 MHz	33.3 MHz	33.33 MHz	33.333 MHz	33.3333 MHz
33.33333 MHz	37.5 MHz	38 MHz	38.4 MHz	40 MHz	40.5 MHz	48 MHz	50 MHz	54 MHz
60 MHz	62.5 MHz	65 MHz	66 MHz	66.6 MHz	66.66 MHz	66.666 MHz	66.6666 MHz	66.66666 MHz
72 MHz	74.175824 MHz	74.176 MHz	74.25 MHz	75 MHz	77.76 MHz			

#### Note:

## Ordering Codes for Supported Tape & Reel Packing Method<sup>[13]</sup>

Device Size	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
2.0 x 1.6 mm	D	E	-	-	-	-
2.5 x 2.0 mm	D	E	-	-	-	-
3.2 x 2.5 mm	D	E	-	-	-	-
5.0 x 3.2 mm	-	-	Т	Y	-	-
7.0 x 5.0 mm	-	-	-	-	Т	Y

#### Note:

<sup>12.</sup> Contact SiTime for frequencies that are not listed in the above table.

<sup>13.</sup> For "-", contact SiTime for availability.

## Low Power, Standard Frequency Oscillator



### Additional Information

Document	Description	Download Link
Time Machine II	MEMS oscillator programmer	http://www.sitime.com/support/time-machine-oscillator-programmer
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	http://www.sitime.com/component/docman/doc_download/85-manu facturing-notes-for-sitime-oscillators
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes

## **Revision History**

Version	Release Date	Change Summary
1.0	2/8/13	Preliminary Information
1.1	7/24/13	<ul> <li>Added programmable drive strength</li> <li>Added the Time Machine and FP device info</li> <li>Added performance plots</li> <li>Removed all footnotes related to softedge</li> </ul>
1.2	3/26/15	Added 20 MHz to frequency selection

© SiTime Corporation 2015. The information contained herein is subject to change at any time without notice. SiTime assumes no responsibility or liability for any loss, damage or defect of a Product which is caused in whole or in part by (i) use of any circuitry other than circuitry embodied in a SiTime product, (ii) misuse or abuse including static discharge, neglect or accident, (iii) unauthorized modification or repairs which have been soldered or altered during assembly and are not capable of being tested by SiTime under its normal test conditions, or (iv) improper installation, storage, handling, warehousing or transportation, or (v) being subjected to unusual physical, thermal, or electrical stress.

Disclaimer: SiTime makes no warranty of any kind, express or implied, with regard to this material, and specifically disclaims any and all express or implied warranties, either in fact or by operation of law, statutory or otherwise, including the implied warranties of merchantability and fitness for use or a particular purpose, and any implied warranty arising from course of dealing or usage of trade, as well as any common-law duties relating to accuracy or lack of negligence, with respect to this material, any SiTime product and any product documentation. Products sold by SiTime are not suitable or intended to be used in a life support application or component, to operate nuclear facilities, or in other mission critical applications where human life may be involved or at stake. All sales are made conditioned upon compliance with the critical uses policy set forth below.

### CRITICAL USE EXCLUSION POLICY

BUYER AGREES NOT TO USE SITIME'S PRODUCTS FOR ANY APPLICATION OR IN ANY COMPONENTS USED IN LIFE SUPPORT DEVICES OR TO OPERATE NUCLEAR FACILITIES OR FOR USE IN OTHER MISSION-CRITICAL APPLICATIONS OR COMPONENTS WHERE HUMAN LIFE OR PROPERTY MAY BE AT STAKE.

SiTime owns all rights, title and interest to the intellectual property related to SiTime's products, including any software, firmware, copyright, patent, or trademark. The sale of SiTime products does not convey or imply any license under patent or other rights. SiTime retains the copyright and trademark rights in all documents, catalogs and plans supplied pursuant to or ancillary to the sale of products or services by SiTime. Unless otherwise agreed to in writing by SiTime, any reproduction, modification, translation, compilation, or representation of this material shall be strictly prohibited.



# **Supplemental Information**

The Supplemental Information section is not part of the datasheet and is for informational purposes only.



# Silicon MEMS Outperforms Quartz

## Silicon MEMS Outperforms Quartz



### **Best Reliability**

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

### Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- · World-class MEMS and CMOS design expertise

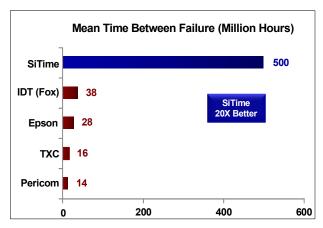


Figure 1. Reliability Comparison<sup>[1]</sup>

### **Best Aging**

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

### Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

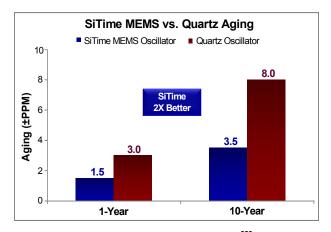


Figure 2. Aging Comparison<sup>[2]</sup>

### **Best Electro Magnetic Susceptibility (EMS)**

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

### Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

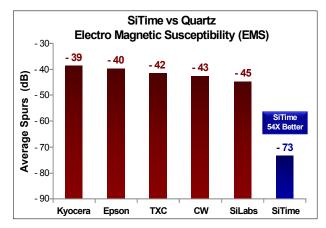


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

### **Best Power Supply Noise Rejection**

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

### Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- · Best analog CMOS design expertise

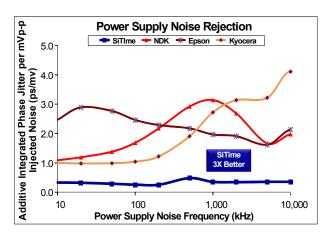


Figure 4. Power Supply Noise Rejection<sup>[4]</sup>

## Silicon MEMS Outperforms Quartz



### **Best Vibration Robustness**

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

### Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

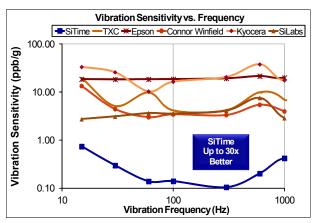


Figure 5. Vibration Robustness<sup>[5]</sup>

#### Notes:

- 1. Data Source: Reliability documents of named companies.
- 2. Data source: SiTime and quartz oscillator devices datasheets.
- 3. Test conditions for Electro Magnetic Susceptibility (EMS):
  - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
  - Field strength: 3V/m
  - Radiated signal modulation: AM 1 kHz at 80% depth
  - Carrier frequency scan: 80 MHz 1 GHz in 1% steps
  - · Antenna polarization: Vertical
  - DUT position: Center aligned to antenna

### Devices used in this test:

SiTime, SiT9120AC-1D2-33E156.250000 - MEMS based - 156.25 MHz

Epson, EG-2102CA 156.2500M-PHPAL3 - SAW based - 156.25 MHz

TXC, BB-156.250MBE-T - 3rd Overtone quartz based - 156.25 MHz

Kyocera, KC7050T156.250P30E00 - SAW based - 156.25 MHz

Connor Winfield (CW), P123-156.25M - 3rd overtone quartz based - 156.25 MHz

SiLabs, Si590AB-BDG - 3rd overtone quartz based - 156.25 MHz

4. 50 mV pk-pk Sinusoidal voltage.

### Devices used in this test:

SiTime, SiT8208AI-33-33E-25.000000, MEMS based - 25 MHz

NDK, NZ2523SB-25.6M - quartz based - 25.6 MHz

Kyocera, KC2016B25M0C1GE00 - quartz based - 25 MHz

Epson, SG-310SCF-25M0-MB3 - quartz based - 25 MHz

- 5. Devices used in this test: same as EMS test stated in Note 3.
- 6. Test conditions for shock test:
  - MIL-STD-883F Method 2002
  - Condition A: half sine wave shock pulse, 500-g, 1ms
  - $\bullet$  Continuous frequency measurement in 100  $\mu s$  gate time for 10 seconds

Devices used in this test: same as EMS test stated in Note 3

7. Additional data, including setup and detailed results, is available upon request to qualified customers. Please contact productsupport@sitime.com.

### **Best Shock Robustness**

SiTime's oscillators can withstand at least  $50,000\ g$  shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

### Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

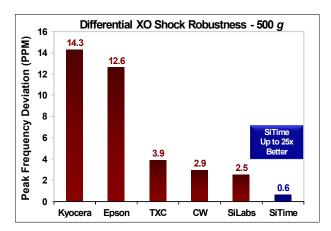


Figure 6. Shock Robustness<sup>[6]</sup>

## **Document Feedback Form**



SiTime values your input in improving our documentation. Click <u>here</u> for our online feedback form or fill out and email the form below to <u>productsupport@sitime.com</u>.

1. Does the Electrical Characteristics table provide complete information?			Yes	No		
If No, what paramete	ers are missing?					
2. Is the organization of this document easy to follow?			Yes	No		
If "No," please sugge	est improvements that we can make:					
3. Is there any applic	ation specific information that you would like	e to see in this o	document? (Ch	eck all that appl	y)	
EMI	EMI Termination recommendations Shock an			nd vibration performance		
If "Other," please spe	ecify:					
4. Are there any errors in this document? Yes			No			
If "Yes", please spec	ify (what and where):					
5. Do you have addit	ional recommendations for this document?					
Name						
Title						
Company						
Address						
City / State or Provin	ce / Postal Code / Country					
Telephone						
Application						
Would you like a rep	ly? Yes No					

Thank you for your feedback. Please click the email icon in your Adobe Reader tool bar and send to <a href="mailto:productsupport@sitime.com">productsupport@sitime.com</a>. Or you may use our <a href="mailto:online-feedback">online-feedback form</a>.

Feedback Form Rev. 1.0 www.sitime.com

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Standard Clock Oscillators category:

Click to view products by SiTime manufacturer:

Other Similar products are found below:

601252 F335-25 F535L-33.333 F535L-50 ASV-20.000MHZ-LR-T ECS-2018-160-BN-TR MXO45HS-2C-66.6666MHZ SiT1602BI-22-33E-50.000000E SiT8209AI-32-33E-125.000000 SIT8918AA-11-33S-50.000000G SM4420TEV-40.0M-T1K SMA4306-TL-H F335-24 F535L-40 F535L-10 F535L-12 F535L-16 F535L-24 F535L-27 F535L-48 PE7744DW-100.0M ASF1-3.686MHZ-N-K-S ASV-4.000MHZ-LCS-T XLH735025.000JU4I8 XLP725125.000JU6I8 XO57CTECNA3M6864 ECS-2100A-147.4 601251 EP16E7E2H26.000MTR SiT8503AI-18-33E-0.200000X SIT8918AA-11-33S-16.000000G SIT9122AI2C233E300.000000X XO37CTECNA20M XO3003 9120AC-2D2-33E212.500000 9102AI-243N25E100.00000 8208AC-82-18E-25.00000 ASDK2-32.768KHZ-LR-T3 8008AI-72-XXE-24.545454E 8004AC-13-33E-133.33000X AS-4.9152-16-SMD-TR ASFL1-48.000MHZ-LC-T 632L31004M00000 SIT8920AM-31-33E-25.0000 DSC1028DI2-019.2000 9121AC-2C3-25E100.00000 9102AI-233N33E100.000000X 9102AI-233N25E200.00000 9102AI-232H25S125.00000 9102AI-133N25E200.00000